

# Quantum Well Gain (first sub-band)

$$g(\hbar\omega) = C_0 |\hat{e} \cdot \vec{P}_{cv}|^2 P_{r,2D}(\hbar\omega) \cdot H(\hbar\omega - E_{ni}) (f_c - f_v)$$

$\uparrow$  Polarization, dep  
 $\uparrow$   $\frac{m_r^*}{\pi \hbar^2 L_z}$   
 $\uparrow$  step Function

In QW., first subband

$$n = N_1 = \int P_{r,2D} \cdot f_c dE = \int_0^\infty \frac{m_e^*}{\pi \hbar^2 L_z} \cdot \frac{d\chi}{1 + e^\chi} \quad ; \quad \chi = \frac{E - F_c}{kT}$$

$$= n_c \ln \left( 1 + e^{\frac{F_c - E_c - E_{e1}}{kT}} \right)$$

$\uparrow$   
 $\frac{m_e^* k_B T}{\pi \hbar^2 L_z}$  effective D.O.S  
 $\uparrow$  Lumped

$$F_c \gg E_c + E_{e1}$$

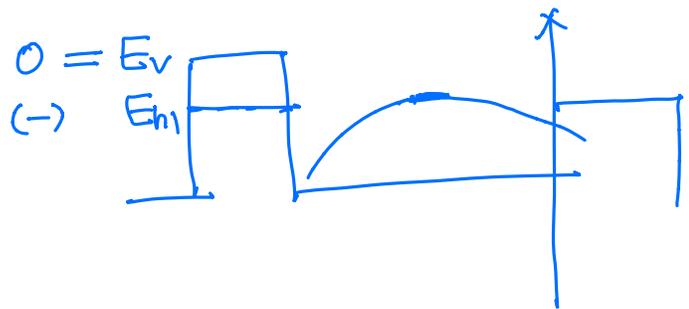
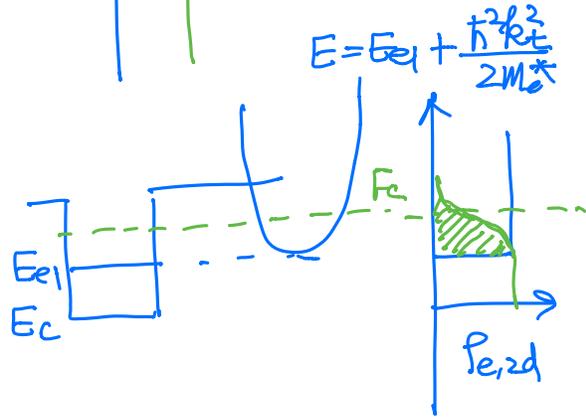
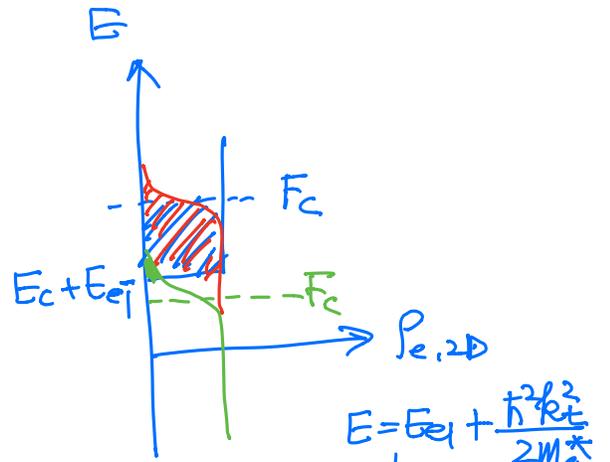
$$N_1 = n_c \cdot \frac{F_c - E_c - E_{e1}}{k_B T}$$

$$F_c \ll E_c + E_{e1}$$

$$N_1 = n_c \cdot \ln(1 + \epsilon) \approx n_c \epsilon$$

$$= n_c e^{\frac{F_c - E_c - E_{e1}}{k_B T}}$$

$$P = n_v \cdot \ln \left( 1 + e^{\frac{E_{h1} - F_v}{kT}} \right)$$





GaAs :  $\Delta = 2.15$  ,  $N = 9 \times 10^{17} \text{ cm}^{-3}$

\* No significant difference in  $N_{tr}$  in Bulk or QW

↑  
Transparency Carrier Conc.

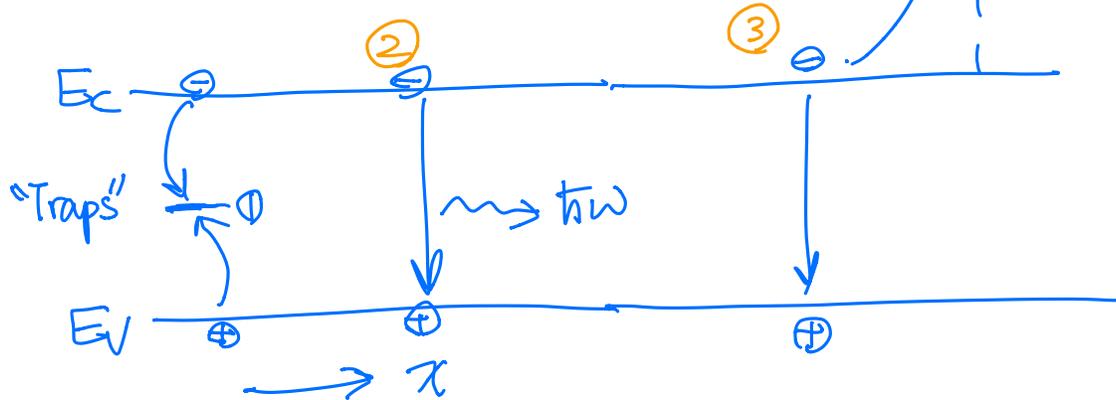
General  $J = \underbrace{A \cdot N}_{\text{SRH}} + \underbrace{B N^2}_{\text{Radiative recombination}} + \underbrace{C N^3}_{\text{Auger Recomb.}}$

$N > N_{tr}$

① SRH (Non-radiative recombination)

②  $e^-$  energetic elec. Radiative recombination

③ Auger Recomb.



$J \propto C N^3$  in typical InGaAsP laser

at NIR  $\lambda \sim 1.55 \mu\text{m}$

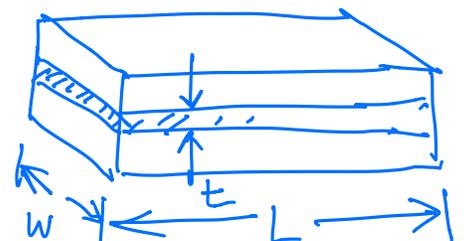
Reduce Power consumption

$P_{cons} = V \cdot I \propto V \cdot \text{Area} \cdot C N^3 > V \cdot \text{Area} \cdot C N_{tr}^3$

Threshold current , when  $N = N_{th} > N_{tr}$

$I = \frac{N_{th} \cdot V_{active}}{\tau} \cdot q$

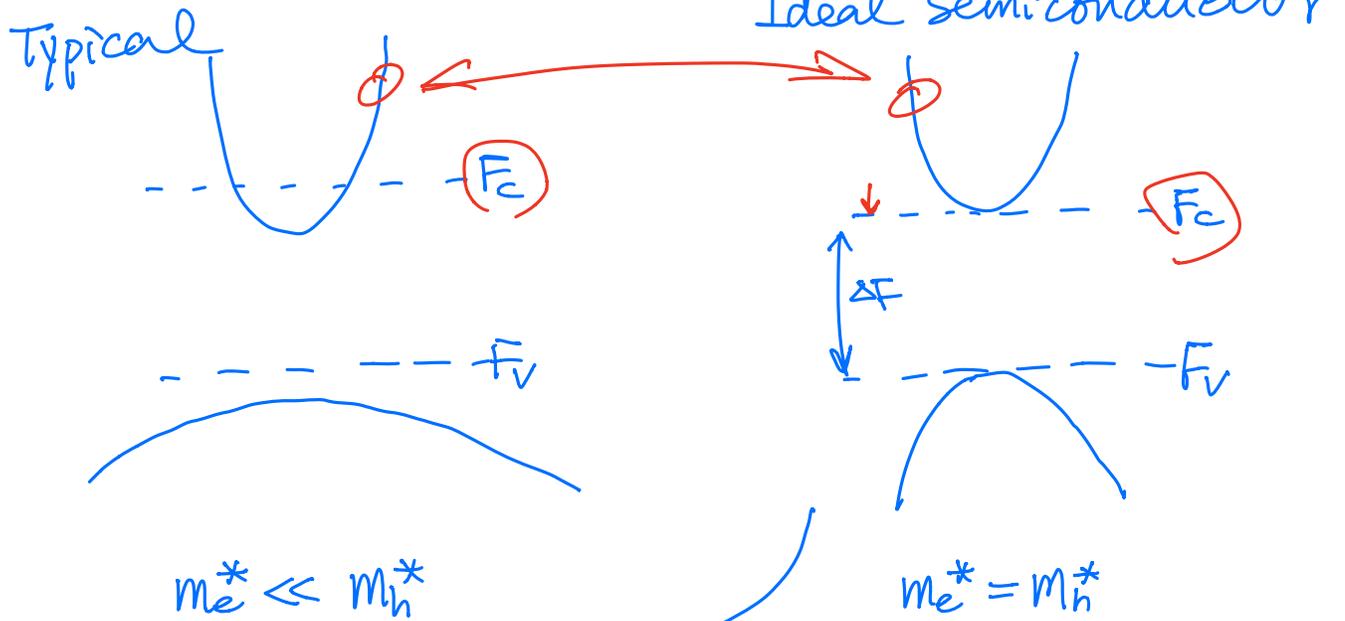
$\tau$  carrier lifetime



Bulk  $V_{active} = w \cdot L \cdot t$  ,  $t \sim 100 \text{ nm}$

- QW  $V_{active} = W \cdot L \cdot L_z$ ,  $L_z < 10 \text{ nm}$
- Have lower threshold current
  - Lower Power consumption
  - ⇒ Almost all lasers are QW

### Strained Quantum Well Lasers:



$N_{tr}(Ideal) < N_{tr}(typical)$

$$N_s = N_i \cdot L_z = \frac{m_e^* k_B T}{\pi \hbar^2} \ln(1 + e^{\frac{F_c - E_c - E_{e1}}{k_B T}})$$

$F_c = E_c + E_{e1}$

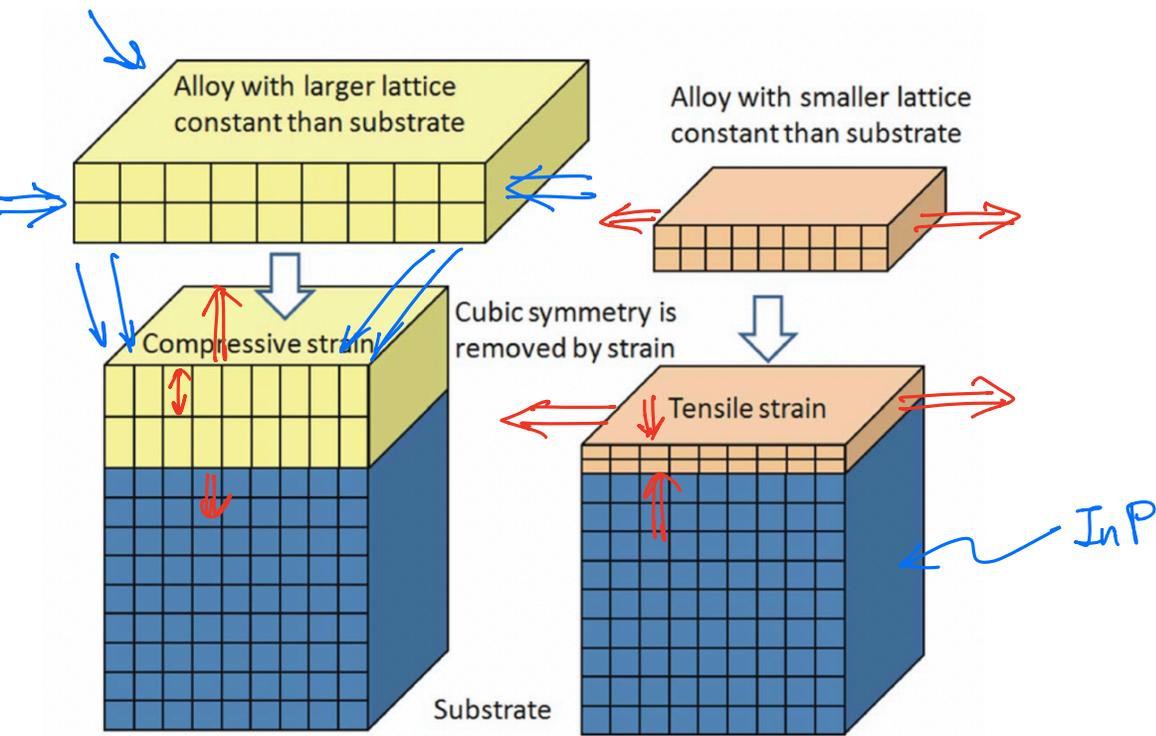
$$N_s = N_i \cdot L_z \cdot \ln 2 = \frac{m_e^* k_B T}{\pi \hbar^2} \ln 2$$

$[\frac{1}{cm^2}]$

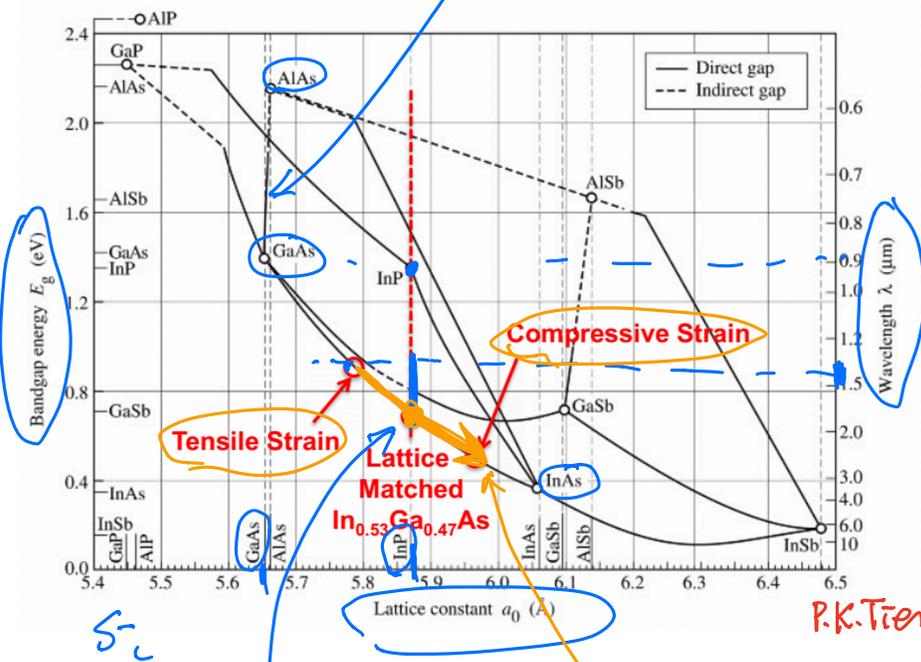
Previously  $N_s(GaAs) = \frac{m_e^* k_B T}{\pi \hbar^2} \times 1.56$

$$\frac{N_{s, tr. typical}}{N_{s, tr. ideal}} = \frac{1.56}{\ln 2} \approx 2$$

$J \propto CN^3$  2x reduction in N  
 ⇒ 8x reduction in current.



$$(AlAs)_x(GaAs)_{1-x} = Al_xGa_{1-x}As$$

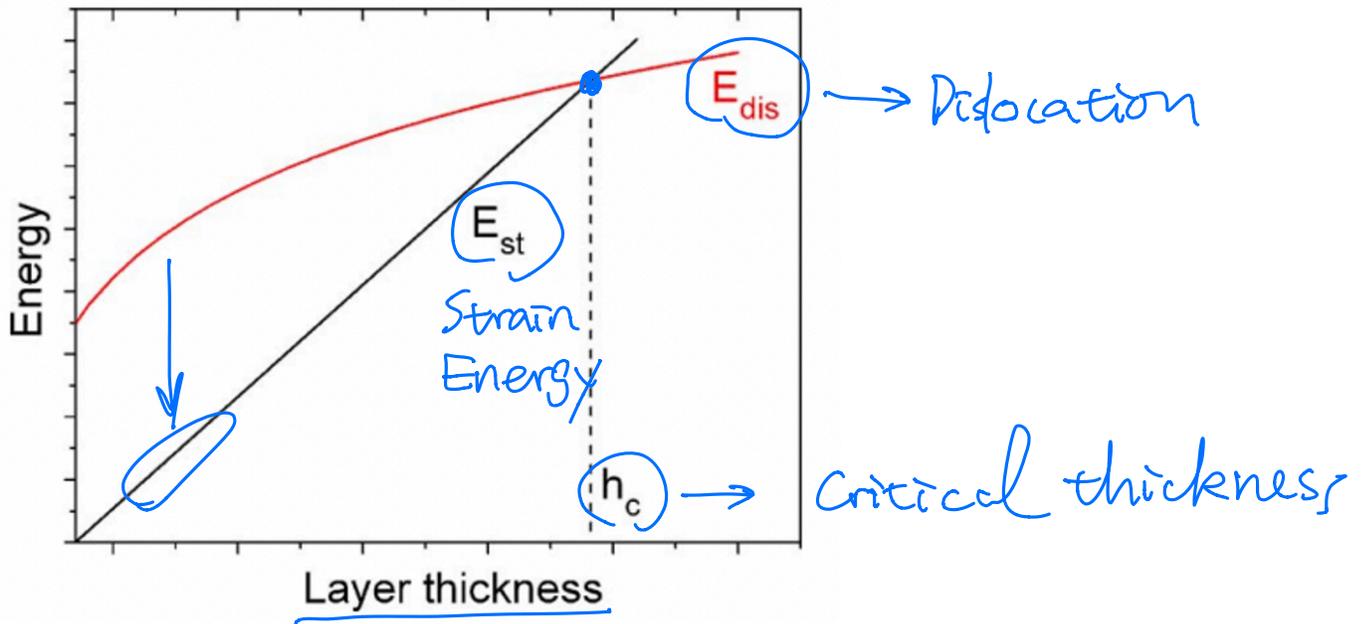


GaAs  $\rightarrow$  870 nm

$\rightarrow$  1310 nm

1550 nm

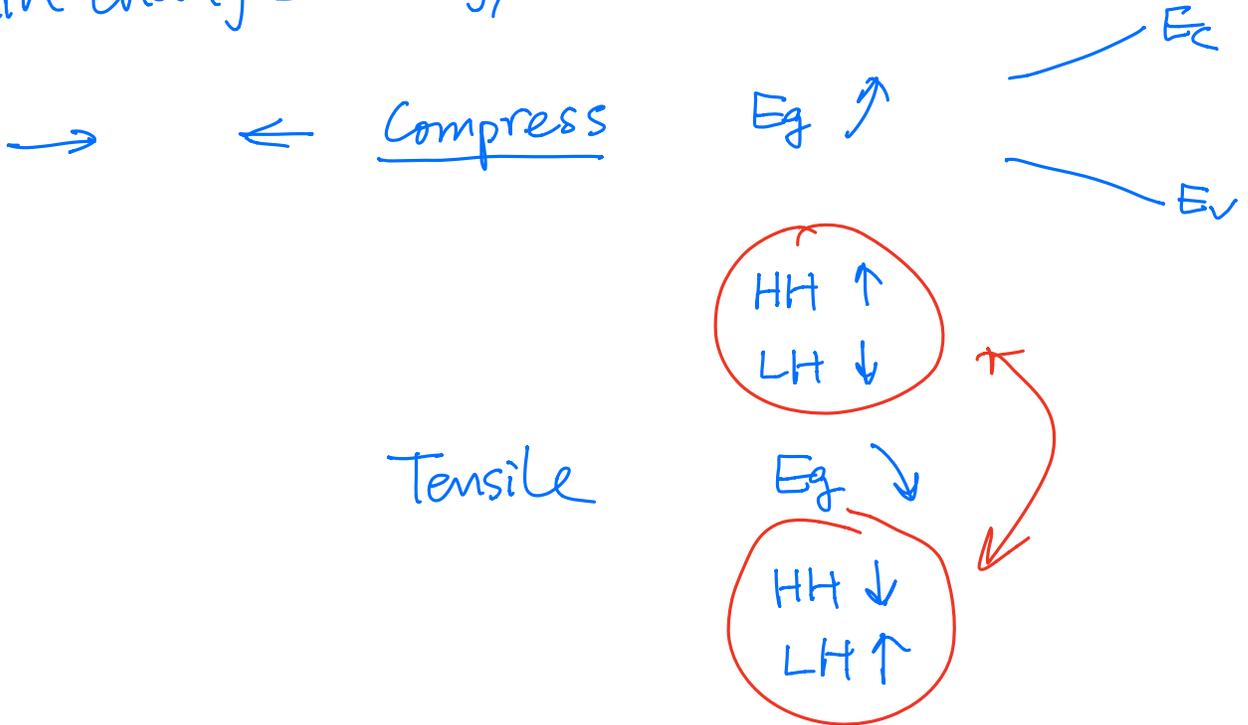


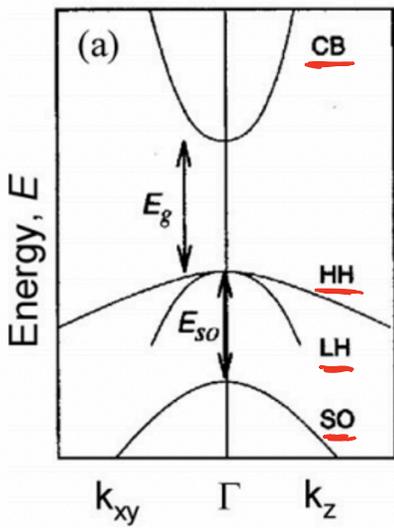


“Coherent” strain  
↳ like rubberband

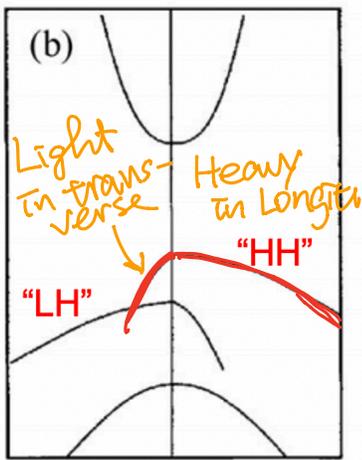
“Relaxed”

Strain change energy band, valence band





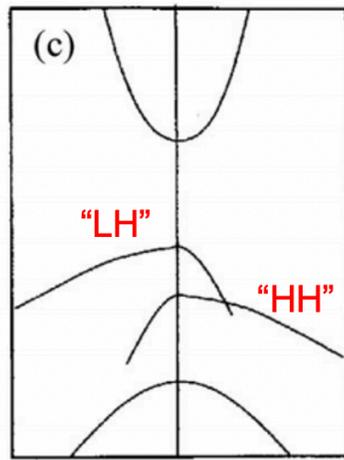
Unstrained



Compressive Strain

Strain break  
symm.

$k_x$  or  $k_y$   
Transverse



Tensile Strain

longitudinal

